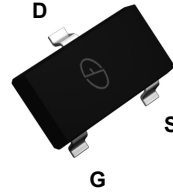
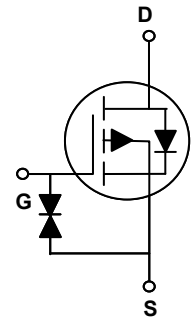


Main Product Characteristics

$V_{(BR)DSS}$	-60V
$R_{DS(on)}$	$4\Omega @ V_{GS} = -10V$
I_D	-0.3A



SOT-323



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for load switch, hand-held devices and LED applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The BSS84AKW utilizes the latest techniques to achieve high cell density, low on-resistance and high repetitive avalanche rating. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current – Continuous ($T_A = 25^\circ\text{C}$)	I_D	-0.3	A
Drain Current – Continuous ($T_A = 70^\circ\text{C}$)		-0.24	A
Drain Current – Pulsed ¹	I_{DM}	-0.6	A
Power Dissipation ($T_A = 25^\circ\text{C}$)	P_D	0.27	W
Power Dissipation – Derate above 25°C	P_D	2.16	mW/ $^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	---	450	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=-1\text{mA}$	---	0.03	---	$V/^{\circ}\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=125^{\circ}\text{C}$	---	---	-30	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 10	μA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-0.3A$	---	2.3	4	Ω
		$V_{GS}=-4.5V, I_D=-0.2A$	---	2.9	5	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1	-1.5	-2	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-2.1	---	$\text{mV}/^{\circ}\text{C}$
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V, F=1\text{MHz}$	---	41	---	μF
Output Capacitance	C_{oss}		---	13	---	
Reverse Transfer Capacitance	C_{rss}		---	8	---	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	---	---	-0.3	A
Pulsed Source Current	I_{SM}		---	---	-0.6	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	-1.3	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

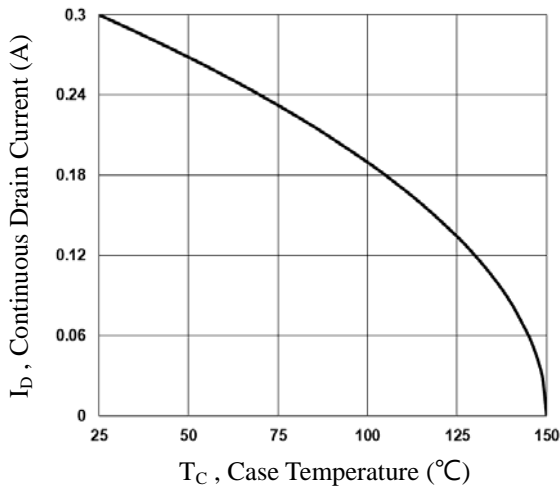


Fig.1 Continuous Drain Current vs. T_C

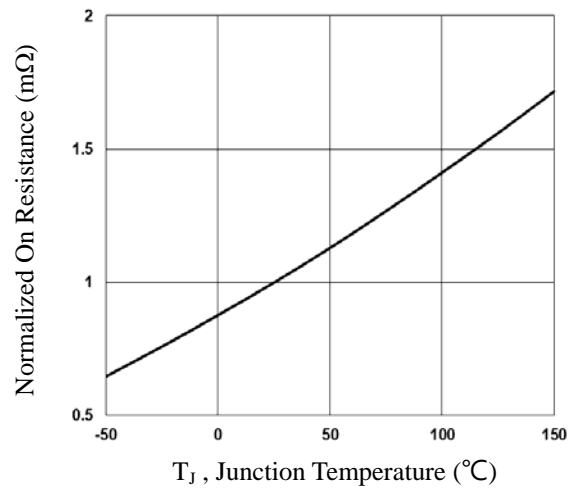


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

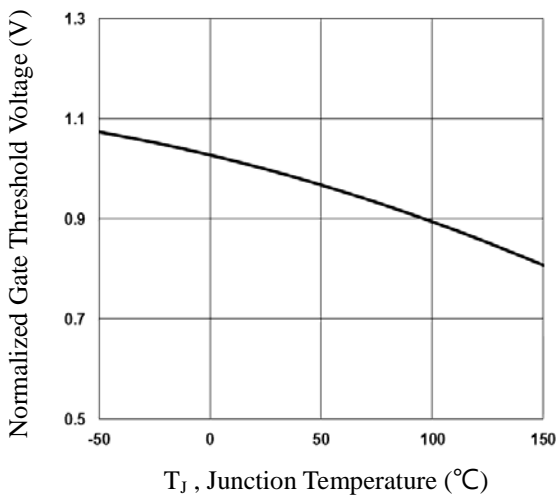


Fig.3 Normalized V_{th} vs. T_J

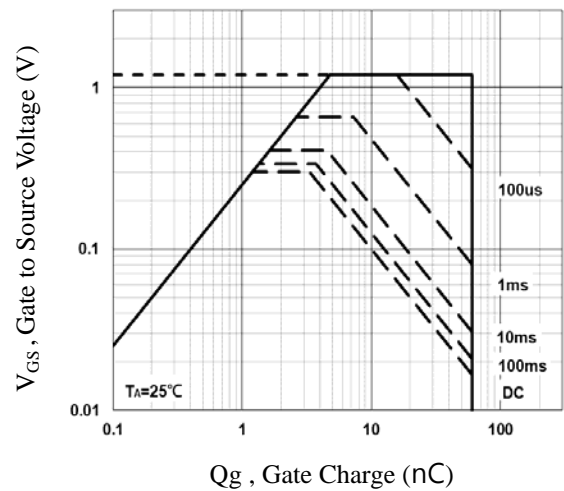


Fig.4 Gate Charge Waveform

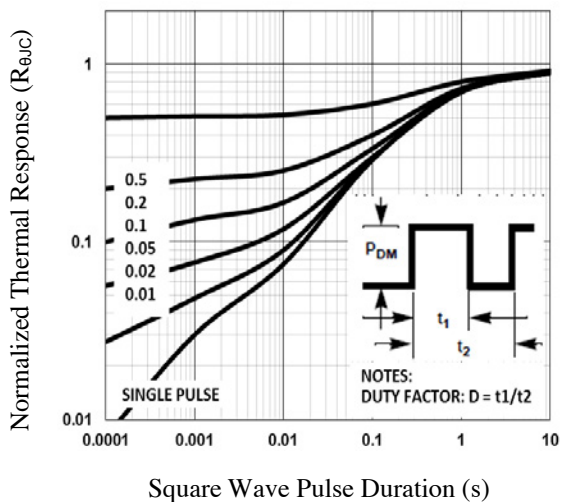


Fig.5 Normalized Transient Impedance

Typical Electrical and Thermal Characteristic Curves

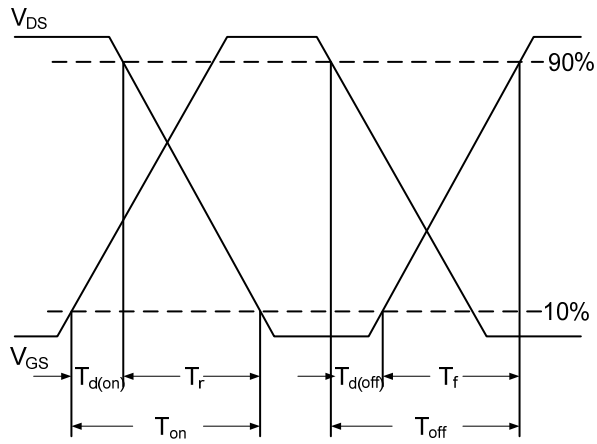


Fig. 6 Switching Time Waveform

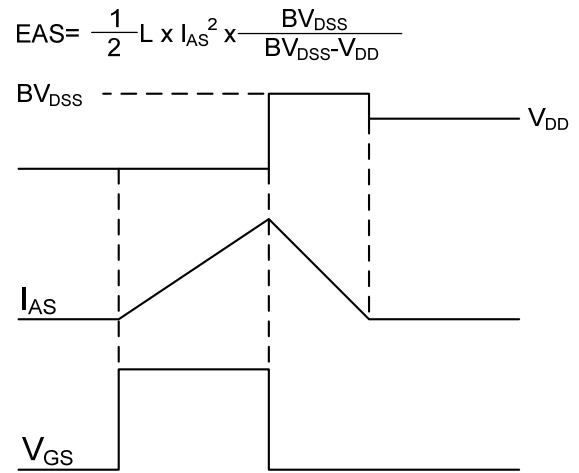
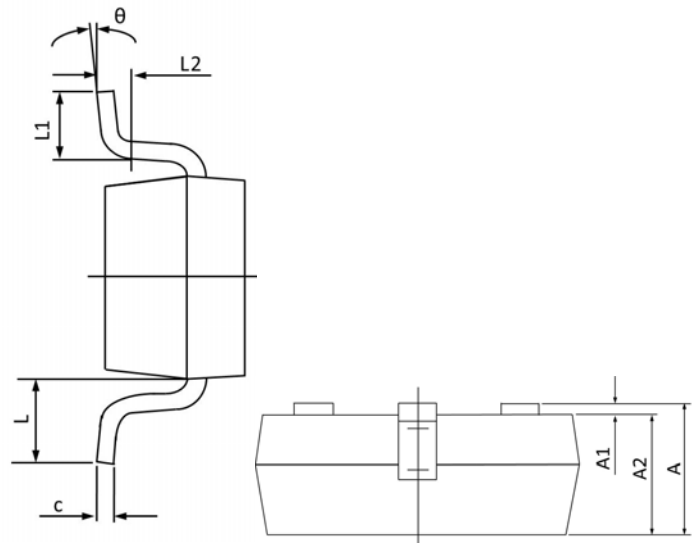
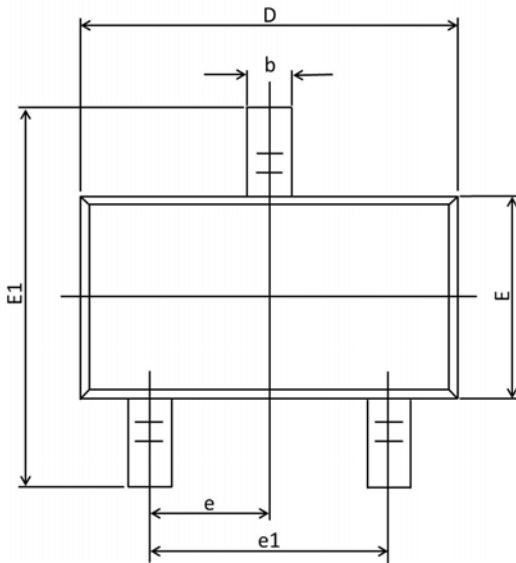


Fig.7 EAS Waveform



Package Outline Dimensions

SOT-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A 1	0.100	0.000	0.004	0.000
A 2	1.000	0.800	0.039	0.031
b	0.400	0.200	0.016	0.008
c	0.250	0.080	0.010	0.003
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E 1	2.450	1.800	0.096	0.071
e	0.65BSC		0.026BSC	
e 1	1.400	1.200	0.055	0.047
L	0.525REF.		0.021REF.	
L 1	0.460	0.150	0.018	0.006
L 2	0.200	0.000	0.008	0.000
θ	8°	0°	8°	0°